N-Channel Super Junction Power MOSFET Ⅱ

General Description

The series of devices use advanced super junction technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

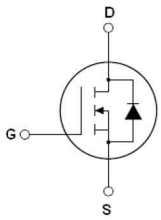
Features

- ◆ New technology for high voltage device
- ◆ Low on-resistance and low conduction losses
- ◆ Small package
- ◆ Ultra Low Gate Charge cause lower driving requirements
- ◆ 100% Avalanche Tested
- ◆ ROHS compliant

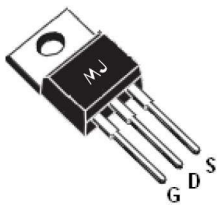
Application

- ◆ Power factor correction（PFC）
- ◆ Switched mode power supplies(SMPS)
- ◆ Uninterruptible Power Supply（UPS）

V_{DS}	650	V
$R_{DS(ON)\ MAX}$	360	mΩ
I_D	11	A



Schematic diagram



TO-220

Package Marking And Ordering Information

Device	Device Package	Marking
MJ65R360	TO-220	MJ65R360

Table 1. Absolute Maximum Ratings (T_C=25℃)

Parameter	Symbol	MJ65R360	Unit
Drain-Source Voltage (V_{GS}=0V)	V_{DS}	650	V
Gate-Source Voltage (V_{DS}=0V)	V_{GS}	±30	V
Continuous Drain Current at Tc=25°C	$I_{D\ (DC)}$	11	A
Continuous Drain Current at Tc=100°C	$I_{D\ (DC)}$	7	A
Pulsed drain current (Note 1)	$I_{DM\ (pluse)}$	33	A
Maximum Power Dissipation (Tc=25℃)	P_D	121	W
Derate above 25°C	P_D	0.97	W/°C
Single pulse avalanche energy (Note 2)	E_{AS}	280	mJ
Avalanche current (Note 1)	I_{AR}	5.5	A
Repetitive Avalanche energy, t_{AR} limited by T_{jmax} (Note 1)	E_{AR}	0.5	mJ

Parameter	Symbol	MJ65R360	Unit
Drain Source voltage slope, V_{DS} ≤480 V	dv/dt	50	V/ns
Reverse diode dv/dt, V_{DS} ≤480 V,I_{SD}<I_D	dv/dt	15	V/ns
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55...+150	°C

* limited by maximum junction temperature

Table 2. Thermal Characteristic

Parameter	Symbol	MJ65R360	Unit
Thermal Resistance，Junction-to-Case（Maximum）	R_{thJC}	1.03	°C/W
Thermal Resistance，Junction-to-Ambient（Maximum）	R_{thJA}	62	°C/W

Table 3. Electrical Characteristics (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	650	-	-	V
Zero Gate Voltage Drain Current (Tc=25℃)	I_{DSS}	V_{DS}=650V,V_{GS}=0V	-	0.05	1	μA
Zero Gate Voltage Drain Current (Tc=125℃)	I_{DSS}	V_{DS}=650V,V_{GS}=0V	-	-	100	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±30V,V_{DS}=0V	-	-	±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	2.5	3	3.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V,I_D=7A	-	300	360	mΩ
Dynamic Characteristics						
Forward Transconductance	g_{FS}	V_{DS}=20V,I_D=7A	-	8	-	S
Input Capacitance	C_{ies}	V_{DS}=50V,V_{GS}=0V F=1.0MHz	-	1030	-	PF
Output Capacitance	C_{oss}		-	87	-	PF
Reverse Transfer Capacitance	C_{rss}		-	4.5	-	PF
Total Gate Charge	Q_g	V_{DS}=480V,I_D=11A V_{GS}=10V	-	23	40	nC
Gate-Source Charge	Q_{gs}		-	5.7	-	nC
Gate-Drain Charge	Q_{gd}		-	8	-	nC
Intrinsic gate resistance	R_G	f=1 MHz open drain	-	2	-	Ω
Switching times						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=380V,I_D=5.5A R_G=6.8Ω,V_{GS}=10V	-	9	-	nS
Turn-on Rise Time	t_r		-	4	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	40	65	nS
Turn-Off Fall Time	t_f		-	4.5	8	nS
Source- Drain Diode Characteristics						
Source-drain current (Body Diode)	I_{SD}	T_C=25°C	-	-	11	A
Pulsed Source-drain current (Body Diode)	I_{SDM}		-	-	33	A
Forward On Voltage	V_{SD}	T_j=25°C,I_{SD}=11A,V_{GS}=0V	-	0.9	1.2	V
Reverse Recovery Time	t_{rr}	T_j=25°C,I_F=11A di/dt=100A/μs	-	245	-	nS
Reverse Recovery Charge	Q_{rr}		-	2.4	-	uC
Peak reverse recovery current	I_{rrm}		-	20	-	A

Notes

1.Repetitive Rating: Pulse width limited by maximum junction temperature

2.T_j=25℃,V_{DD}=50V,V_G=10V, R_G=25Ω

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

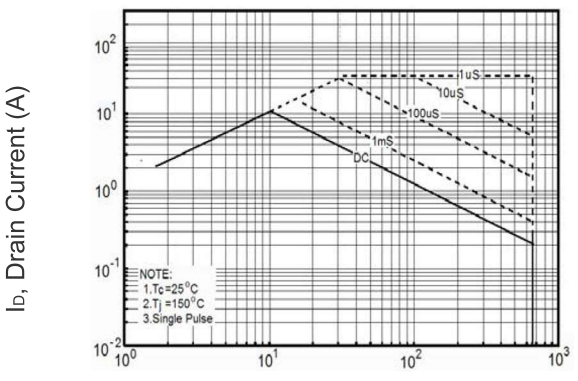


Figure 1 Safe operating area

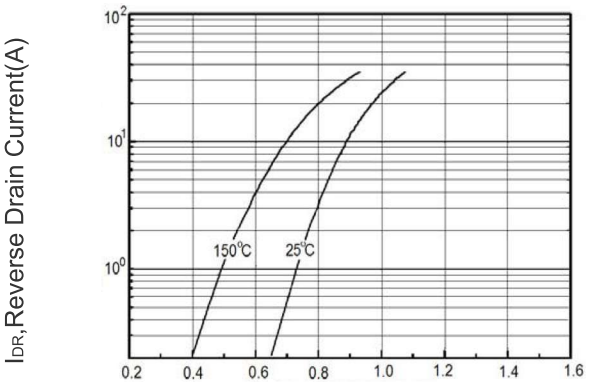


Figure 2 Source-Drain Diode Forward Voltage

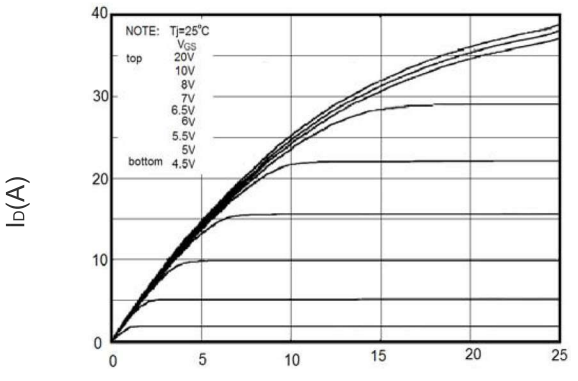


Figure 3 Output characteristics

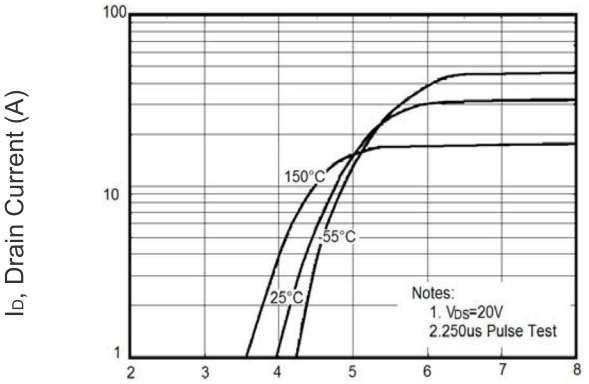


Figure 4 Transfer characteristics

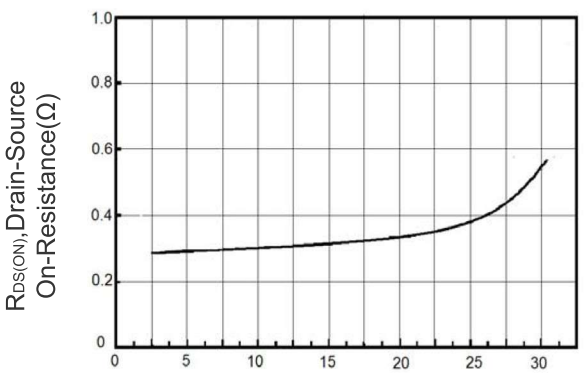


Figure 5 Static drain-source on resistance

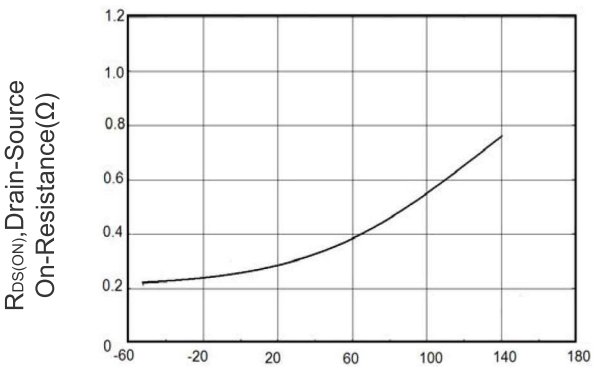


Figure 6 $R_{DS(ON)}$ vs Junction Temperature

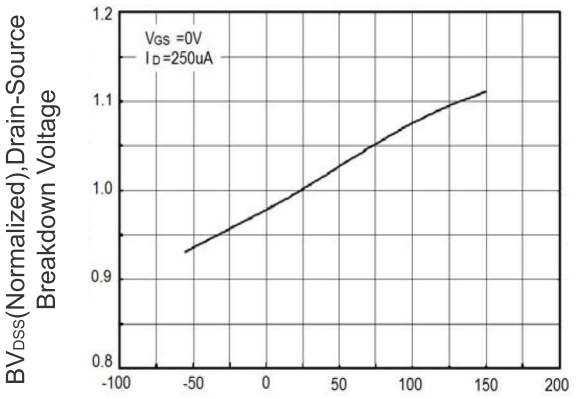


Figure 7 BV_{DSS} vs Junction Temperature

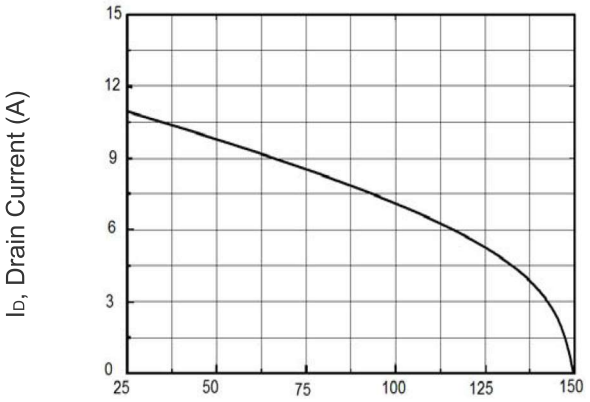


Figure 8 Maximum I_D vs Junction Temperature

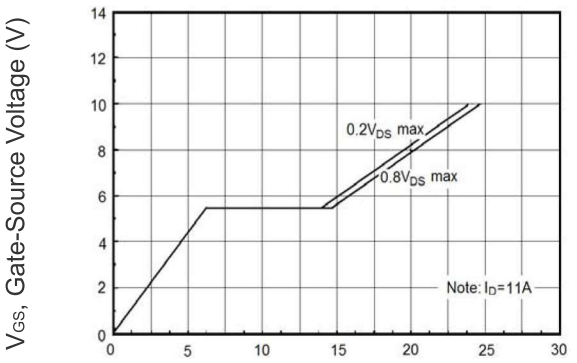


Figure 9 Gate charge waveforms

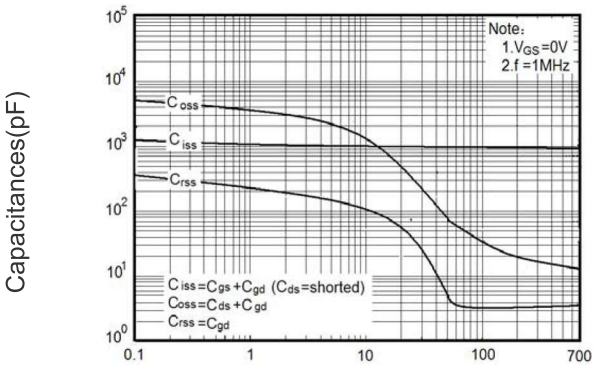


Figure 10 Capacitance

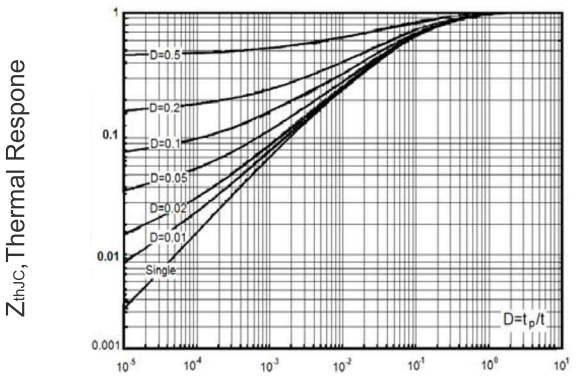
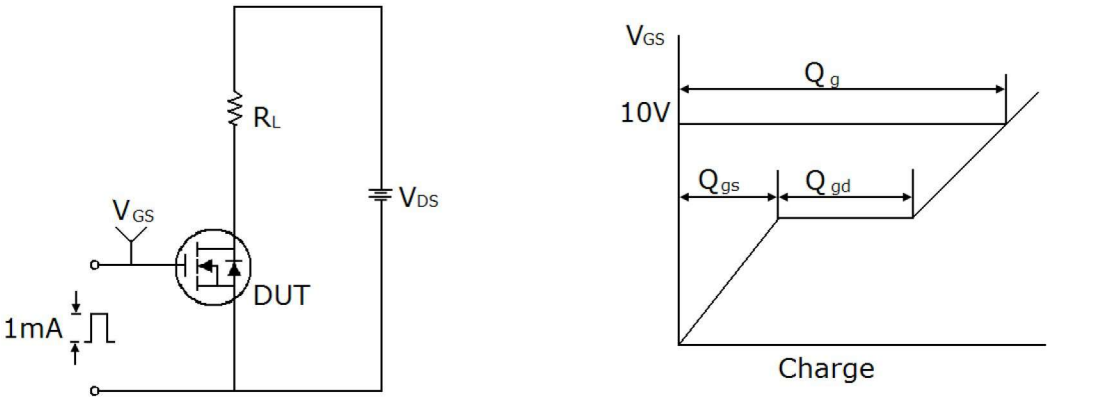
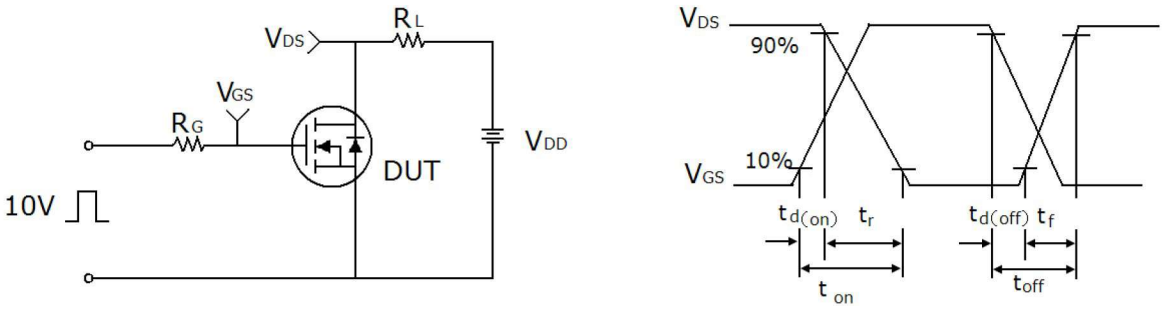


Figure 11 Transient Thermal Impedance

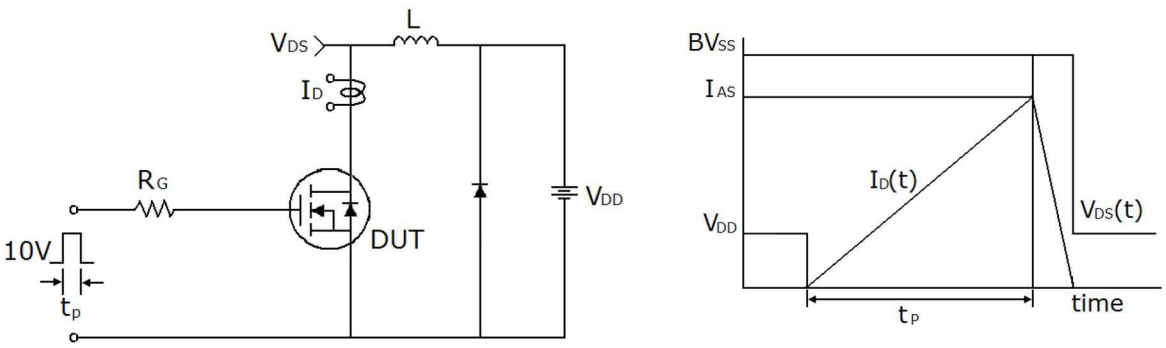
Test circuit



Gate charge test circuit & Waveform

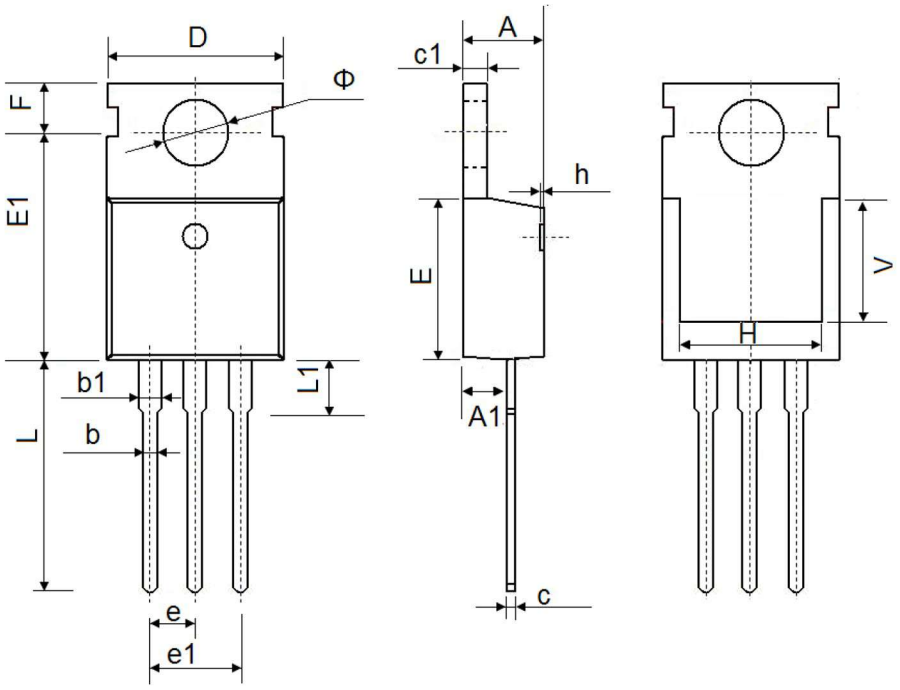


Switch Time Test Circuit



Unclamped Inductive Switching Test Circuit & Waveforms

TO-220-3L-C Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	7.500 REF.		0.295 REF.	
Φ	3.400	3.800	0.134	0.150

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